

INFORMATION DISCLOSURE CITATION	ATTY. DOCKET NO. <u>O I P 925-178</u>	SERIAL NO. <u>09/463,643</u>
APPLICANT <u>KAMURA et al</u>		
(Use several sheets if necessary)	FILING DATE <u>May 1, 2000</u>	TC/A.U. <u>2815</u>

## **U.S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

Preliminary Notice of Rejection of Japanese Appln. No. 10-199829 (15 Feb. 2005) (including translation)

SUEMUNE, Ikuo, "Doping in a superlattice structure: Improved hole activation in wide-gap II-VI materials," Journal of Applied Physics, U.S.A. American Institute of Physics (March 1, 1990), Vol. 67, No. 5, pp. 2364-2369

\*Examiner

### Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

951921

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U.S. Department of Commerce  
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Attorney Docket No.: NICHIA-00700 | Serial No.:09/463643

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(37 CFR § 1.98(b))

Applicant: Shuji Nakamura, et al.

Filing Date: January 25, 2000

Group Art Unit:

2815

## U.S. PATENT DOCUMENTS

Examiner Initials		Serial / Patent Number	Issue Date	Applicant / Patentee	Class	Subclass	Filing Date
BWN	AA	3566215	2/23/71	Heywang	317	235	7/31/68
	AB	3593191	7/13/71	Henker	331	94.5	9/24/69
	AC	3655439	4/11/72	Seiter	117	212	6/16/69
	AD	3658585	4/25/72	Folkmann, et al.	117	201	2/26/70
	AE	3704427	11/28/72	Heywang	331	94.5	6/3/64
	AF	3705567	12/12/72	Emels	118	49	1/22/71
	AG	3737737	6/5/73	Heywang, et al.	317	234.R	10/6/71
	AH	3747559	7/24/73	Dietze	118	48	5/15/72
	AI	3793984	2/26/74	Kasper, et al.	118	48	11/13/72
	AJ	3819974	6/25/74	Stevenson, et al.	313	499	3/12/73
	AK	3853974	12/10/74	Reuschel, et al.	264	81	2/21/73
	AL	3941647	3/2/76	Druminski	156	612	3/8/73
	AM	3948693	4/6/76	Weyrich, et al.	148	171	7/23/74
	AN	3963537	6/15/76	Kniepkamp, et al.	148	175	8/27/74
	AO	3965347	6/22/76	Heywang	250	211.J	11/12/74
	AP	3974561	8/17/76	Schnoeller	29	611	5/30/74
	AQ	4020791	5/3/77	Reuschel, et al.	118	49.1	11/19/74
	AR	4062035	12/6/77	Winstel	357	17	1/28/77
	AS	4098223	7/4/78	Ertl, et al.	118	48	11/4/76
	AT	4102298	7/25/78	Dietze, et al.	118	5	6/10/76
	AU	4108539	8/22/78	Gort, et al.	350	201	11/18/76
	AV	4113381	9/12/78	Epstein	356	5	11/18/76
	AW	4133702	1/9/79	Krimmel	148	1.5	8/11/77
	AX	4140546	2/20/79	Krimmel	148	1.5	8/17/77
	AY	4154625	5/15/79	Golovchenko et al.	148	1.5	11/16/77
	AZ	4170018	10/2/79	Runge	357	17	3/30/78
	BA	4261770	4/14/81	Splittergerber, et al.	148	171	3/13/80
	BB	4351695	9/28/82	Hieber, et al.	156	603	1/2/81
	BC	4404265	9/13/83	Manasevit	428	689	4/7/78
	BD	4410993	10/18/83	Zschauer	372	44	4/17/81
	BE	4423349	12/27/83	Nakajima, et al.	313	487	7/1/81
	BF	4505765	3/19/85	Trommer	148	171	6/17/83
	BG	4521448	6/4/85	Sasaki	427	88	3/3/83

Examiner:

*B. W. Baum*

Date Considered:

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NB	BH	4531142	7/23/85	Weyrich, et al.	357	17	2/16/83
	BI	4568206	2/4/86	Imazaike	384	530	12/3/84
	BJ	4596998	6/24/86	Krimmel	357	17	7/19/84
	BK	4599244	7/8/86	Falckenberg, et al.	427	74	9/12/84
	BL	4599245	7/8/86	Falckenberg, et al.	427	74	9/11/84
	BM	4604637	8/5/86	Ruhle, et al.	357	17	3/1/83
	BN	4615766	10/7/86	Jackson, et al.	156	662	2/27/85
	BO	4656636	4/7/87	Amann, et al.	372	50	12/23/85
	BP	4661175	4/28/87	Kuphal, et al.	148	171	6/6/85
	BQ	4670093	6/2/87	Maerz, et al.	156	649	4/21/86
	BR	4682337	7/21/87	Amann	372	44	9/13/85
	BS	4683574	7/28/87	Heinen	372	44	9/12/85
	BT	4722088	1/26/88	Wolf	372	44	9/6/85
	BU	4740259	4/26/88	Heinen	156	234	9/15/86
	BV	4742525	5/3/88	Heinen, et al.	372	44	9/6/85
	BW	4744088	5/10/88	Heinen, et al.	372	50	3/13/87
	BX	4746195	5/24/88	Auracher, et al.	350	320	3/13/85
	BY	4763979	8/16/88	Heywang	350	96.20	9/23/86
	BZ	4768199	8/30/88	Heinen, et al.	372	36	9/5/86
	CA	4792200	12/20/88	Amann, et al.	350	96.12	4/1/87
	CB	4792959	12/20/88	Mueller, et al.	372	46	1/30/87
	CC	4818722	4/4/89	Heinen	437	129	5/26/87
	CD	4829188	5/9/89	Shinomiya, et al.	250	483.1	10/1/87
	CE	4835575	5/30/89	Plihal	357	30	2/3/88
	CF	4841344	6/20/89	Heinen	357	17	12/7/87
	CG	4845723	7/4/89	Heinen, et al.	372	38	2/22/88
	CH	4855118	8/8/89	Ichinose, et al.	423	301	4/12/88
	CI	4859903	8/22/89	Minematu, et al.	313	487	3/2/88
	CJ	4864369	9/5/89	Snyder, et al.	357	17	7/5/88
	CK	4869568	9/26/89	Schimpe	350	96.12	9/29/88
	CL	4890033	12/26/89	Ichinomiya, et al.	313	487	6/28/88
	CM	4904617	2/27/90	Muschke	437	129	8/25/88
	CN	4904618	2/27/90	Neumark	437	150	8/22/88
	CO	4907044	3/6/90	Schellhorn, et al.	357	17	7/14/89
	CP	4907534	3/13/90	Huang, et al.	118	725	12/9/88
	CO	4911102	3/27/90	Manabe, et al.	118	719	1/26/88

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BWB	CR	4918497	4/17/90	Edmond	357	17	12/14/88
1	CS	4929907	5/29/90	Berkel	330	252	3/8/89
	CT	4944837	7/31/90	Nishikawa, et al.	156	646	2/28/89
	CU	4945394	7/31/90	Palmour, et al.	357	34	10/26/87
	CV	4946547	8/7/90	Palmour, et al.	156	643	10/13/89
	CW	4947218	8/7/90	Edmond, et al.	357	13	11/3/87
	CX	4959174	9/25/90	Nakajima, et al.	252	301.6R	3/16/89
	CY	4960728	10/2/90	Schaake, et al.	437	82	10/11/88
	CZ	4966862	10/30/90	Edmond	437	100	8/28/89
	DA	4971739	11/20/90	Ichinose, et al.	264	61	4/12/89
	DB	4977567	12/11/90	Hanke	372	45	10/11/89
	DC	4982314	1/1/91	Miki	363	16	12/4/89
	DD	4985742	1/15/91	Pankove	357	34	7/7/89
	DE	4987576	1/22/91	Heinen	372	46	11/3/89
	DF	4990466	2/5/91	Shieh, et al.	437	129	11/1/88
	DG	4990990	2/5/91	Albrecht, et al.	357	30	3/23/88
	DH	5005057	4/2/91	Izumiya, et al.	357	17	4/13/90
	DI	5006908	4/9/91	Matsuoka, et al.	357	17	2/12/90
	DJ	5008735	4/16/91	Edmond, et al.	357	74	12/7/89
	DK	5008789	4/16/91	Arai, et al.	362	255	2/14/90
	DL	5019746	5/28/91	Merg	313	512	12/4/89
	DM	5023686	6/11/91	Helmut, et al.	357	30	6/15/90
	DN	5027168	6/25/91	Edmond	357	17	8/28/89
	DO	5034956	7/23/91	Gessner, et al.	372	45	11/2/89
	DP	5041334	8/20/91	Nakajima, et al.	428	407	12/19/89
	DQ	5042043	8/20/91	Hatano, et al.	372	45	4/13/90
	DR	5045896	9/3/91	Ash, et al.	357	17	3/21/89
	DS	5049779	9/17/91	Itsuki, et al.	313	486	4/28/89
	DT	5061972	10/29/91	Edmond	357	13	9/13/90
	DU	5065207	11/12/91	Heinen	357	30	2/5/91
	DV	5077145	12/31/91	Shinomiya, et al.	428	691	12/21/90
	DW	5093576	3/3/92	Edmond, et al.	250	370.01	3/15/91
	DX	5119540	6/9/92	Kong, et al.	29	25.01	7/24/90
	DY	5120619	6/9/92	Nakajima, et al.	428	690	11/7/90
	DZ	5122845	6/16/92	Manabe, et al.	357	17	2/26/90
BWB	EA	5128955	7/7/92	Danielmeyer	372	94	8/18/88

Examiner:

*Brian Bassett*

Date Considered: 9/15/01

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BWB	EB	5146465	9/8/92	Khan, et al.	372	45	2/1/91
	EC	5155062	10/13/92	Coleman	437	100	12/20/90
	ED	5171370	12/15/92	Reithmaier, et al.	118	726	4/18/90
	EE	5182670	1/26/93	Khan, et al.	359	359	8/30/91
	EF	5184247	2/2/93	Schimppe	359	344	7/17/90
	EG	5185207	2/9/93	Furuoka, et al.	428	404	12/27/91
	EH	5200022	4/6/93	Kong, et al.	156	612	10/3/90
	EI	5202777	4/13/93	Sluzky, et al.	359	50	4/1/92
	EJ	5205905	4/27/93	Kotaki, et al.	156	662	5/30/91
	EK	5208878	5/4/93	Thulke	385	14	10/2/91
	EL	5210051	5/11/93	Carter, Jr.	437	107	6/5/91
	EM	5218216	6/8/93	Manabe, et al.	257	103	12/20/91
	EN	5229626	7/20/93	Ebitani, et al.	257	84	3/27/92
	EO	5233204	8/3/93	Fletcher, et al.	257	13	1/10/92
	EP	5239188	8/24/93	Takeuchi, et al.	257	76	11/4/92
	EQ	5247533	9/21/93	Okazaki, et al.	372	45	12/26/91
	ER	5250366	10/5/93	Nakajima, et al.	428	690	5/8/92
	ES	5252499	10/12/93	Rothschild	437	22	8/15/88
	ET	5252839	10/12/93	Fouquet	257	13	6/10/92
	EU	5260960	11/9/93	Armann, et al.	372	46	4/23/92
	EV	5264713	11/23/93	Palmour	257	77	6/14/91
	EW	5266503	11/30/93	Wang, et al.	437	24	10/2/91
	EX	5270554	12/14/93	Palmour	257	77	6/14/91
	EY	5272108	12/21/93	Kozawa	437	127	2/26/92
	EZ	5278433	1/11/94	Manabe, et al.	257	103	8/7/92
	FA	5281830	1/25/94	Kotaki, et al.	257	86	10/24/91
	FB	5290393	3/1/94	Nakamura	156	613	1/28/92
	FC	5306662	4/26/94	Nakamura, et al.	437	107	11/2/92
	FD	5312560	5/17/94	Somatomo, et al.	252	301.4 S	3/18/93
	FE	5323022	6/21/94	Glass, et al.	257	77	9/10/92
	FF	5330791	7/19/94	Aihara, et al.	427	215	4/16/93
	FG	5334277	8/2/94	Nakamura	117	102	10/22/91
	FH	5336080	8/9/94	Sumitomo, et al.	428	407	12/17/92
	FI	5338944	8/16/94	Edmond, et al.	257	76	9/22/93
	FJ	5341390	8/23/94	Yamada, et al.	372	45	4/15/93
BWB	FK	5343316	8/30/94	Morimoto, et al.	359	50	6/29/93

Examiner: *Brian Frazee*

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bWB	FL	5344791	9/6/94	Huang	437	126	8/14/92
	FM	5359345	10/25/94	Hunter	345	102	8/5/92
	FN	5363390	11/8/94	Yang, et al.	372	22	11/22/93
	FO	5366834	11/22/94	Yoneda, et al.	430	23	5/5/93
	FP	5369289	11/29/94	Tamaki, et al.	257	99	10/30/92
	FQ	5376303	12/27/94	Royce, et al.	252	301.4 R	1/10/94
	FR	5376580	12/27/94	Kish, et al.	437	127	3/19/93
	FS	5381103	1/10/95	Edmond, et al.	324	753	10/13/92
	FT	5382822	1/17/95	Stein	257	410	9/27/93
	FU	5389571	2/14/95	Takeuchi, et al.	437	133	4/16/93
	FV	5390210	2/14/95	Fouquet, et al.	372	92	11/22/93
	FW	5393993	2/28/95	Edmond, et al.	257	77	12/13/93
	FX	5394005	2/28/95	Brown, et al.	257	461	2/18/94
	FY	5403774	4/4/95	Shieh, et al.	437	129	11/6/92
	FZ	5404282	4/4/95	Klinke, et al.	362	249	8/19/94
	GA	5408120	4/18/95	Manabe, et al.	257	431	1/22/93
	GB	5409859	4/25/95	Glass, et al.	437	187	4/22/94
	GC	5416342	5/16/95	Edmond, et al.	257	76	6/23/93
	GD	5417886	5/23/95	Tateiwa, et al.	252	301.4 R	9/20/93
	GE	5433169	7/18/95	Nakamura	117	102	4/6/94
	GF	5433533	7/18/95	Imazaike	384	488	12/20/93
	GG	5433888	7/18/95	Okada, et al.	252	301.4 R	9/20/93
	GH	5435938	7/25/95	Bando, et al.	252	301.4 S	3/10/94
	GI	5438198	8/1/95	Ebitani, et al.	250	330	5/3/94
	GJ	5459107	10/17/95	Palmour	437	238	6/5/92
	GK	5465249	11/7/95	Cooper, Jr. et al.	365	149	11/26/91
	GL	5467291	11/14/95	Fan, et al.	364	578	12/5/91
	GM	5468678	11/21/95	Nakamura, et al.	437	107	1/12/94
	GN	5475241	12/12/95	Harrah, et al.	257	99	10/27/93
	GO	5497012	3/5/96	Moll	257	183	6/15/94
	GP	5502316	3/26/96	Kish, et al.	257	94	10/12/95
	GQ	5506421	4/9/96	Palmour	257	77	11/24/92
	GR	5511084	4/23/96	Amann	372	20	1/17/95
	GS	5514627	5/7/96	Lowery, et al.	437	209	1/24/94
	GT	5523018	6/4/96	Okada, et al.	252	301.4 P	3/23/95
bWB	GU	5523589	6/4/96	Edmond, et al.	257	77	9/20/94

Examiner:

*Susan Brown*

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b7D	GV	5539217	7/23/96	Edmond, et al.	257	77	8/9/93
	GW	5563422	10/8/96	Nakamura, et al.	257	13	4/28/94
	GX	5578839	11/26/96	Nakamura, et al.	257	96	11/17/93
	GY	5583879	12/10/96	Yamazaki, et al.	372	45	4/19/95
	GZ	5585648	12/17/96	Tischler	257	77	2/3/95
	HA	5587593	12/24/96	Koide, et al.	257	94	4/19/95
	HB	5592501	1/7/97	Edmond, et al.	372	45	9/20/94
	HC	5592578	1/7/97	Ruh	385	31	11/1/95
	HD	5596595	1/21/97	Tan, et al.	372	96	6/8/95
	HE	5604135	2/18/97	Edmond, et al.	437	22	8/12/94
	HF	5604763	2/18/97	Kato, et al.	372	45	4/19/95
	HG	5612260	3/18/97	Palmour	437	238	12/9/94
	HH	5614736	3/25/97	Neumann, et al.	257	102	9/25/95
	HI	5616177	4/1/97	Yamada	117	102	2/22/95
	HJ	5620557	4/15/97	Manabe, et al.	438	507	6/26/95
	HK	5621749	4/15/97	Baney	372	69	9/6/95
	HL	5625202	4/29/97	Chai	257	94	6/8/95
	HM	5627244	5/6/97	Sato	526	92	4/26/95
	HN	5629531	5/13/97	Palmour	257	77	12/9/94
	HO	5631190	5/20/97	Negley	438	33	10/7/94
	HP	5635146	6/3/97	Singh, et al.	423	65	11/30/95
	HQ	5642375	6/24/97	King, et al.	372	97	10/26/95
	HR	5650641	7/22/97	Sassa, et al.	257	88	8/31/95
	HS	5652434	7/29/97	Nakamura, et al.	257	13	6/17/96
	HT	5652438	7/29/97	Sassa, et al.	257	94	7/19/95
	HU	5656832	8/12/97	Ohba, et al.	257	190	3/8/95
	HV	5659568	8/19/97	Wang, et al.	372	96	5/23/95
	HW	5661074	8/26/97	Tischler	438	32	5/24/95
	HX	5661316	8/26/97	Kish, Jr., et al.	257	190	9/20/96
	HY	5661742	8/26/97	Huang, et al.	372	46	5/22/96
	HZ	5670798	9/23/97	Schetzina	257	96	3/29/95
	IA	5679153	10/21/97	Dmitriev, et al.	117	106	11/30/94
	IB	5684623	11/4/97	King, et al.	359	346	11/21/96
	IC	5686737	11/11/97	Allen	257	77	9/16/94
	ID	5700713	12/23/97	Yamazaki, et al.	437	129	3/20/95
	IE	5707139	1/13/98	Haitz	362	231	11/1/95

Examiner:

*B. B. Baskin*

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<i>BWB</i>	IF	5718760	2/17/98	Carter, et al.	117	84	2/5/96
	IG	5719409	2/17/98	Singh, et al.	257	77	6/6/96
	IH	5724062	3/3/98	Hunter	345	102	9/21/94
	II	5724373	3/3/98	Chang	372	20	11/15/96
	IJ	5724376	3/3/98	Kish, Jr., et al.	372	96	11/30/95
	IK	5727014	3/10/98	Wang, et al.	372	96	10/31/95
	IL	5729029	3/17/98	Rudaz	257	13	9/6/96
	IM	5729567	3/17/98	Nakagawa	372	99	4/25/96
	IN	5733796	3/31/98	Manabe, et al.	437	127	11/9/95
	IO	5734182	3/31/98	Nakamura, et al.	257	96	6/10/96
	IP	5739552	4/14/98	Kimura, et al.	257	89	10/24/95
	IQ	5739554	4/14/98	Edmond, et al.	257	103	5/8/95
	IR	5741431	4/21/98	Shih	216	65	5/15/97
	IS	5741724	4/21/98	Ramdani, et al.	437	128	12/27/96
	IT	5742133	4/21/98	Wilhelm, et al.	315	291	9/9/96
	IU	5747832	5/5/98	Nakamura, et al.	257	103	6/10/96
	IV	5753939	5/19/98	Sassa, et al.	257	94	3/7/97
	IW	5758951	6/2/98	Haitz	362	259	6/27/97
	IX	5761229	6/2/98	Baldwin, et al.	372	31	1/25/96
	IY	5767581	6/16/98	Nakamura, et al.	257	749	6/17/96
	IZ	5771254	6/23/98	Baldwin, et al.	372	31	6/3/96
	JA	5776837	7/7/98	Palmour	438	767	11/19/96
	JB	5777350	7/7/98	Nakamura, et al.	257	96	11/30/95
	JC	5777433	7/7/98	Lester, et al.	313	512	7/11/96
	JD	5779924	7/14/98	Krames, et al.	216	24	3/22/96
	JE	5780120	7/14/98	Belouet, et al.	427	554	12/18/96
	JF	5785404	7/28/98	Wiese	362	32	6/29/95
	JG	5793054	8/11/98	Nido	257	18	6/13/96
	JH	5793062	8/11/98	Kish, Jr., et al.	257	98	10/24/97
	JI	5805624	9/8/98	Yang, et al.	372	45	7/30/96
	JJ	5808323	9/15/98	Spaeth, et al.	257	88	3/29/96
	JK	5808592	9/15/98	Mizutani, et al.	345	83	4/21/95
	JL	5809050	9/15/98	Baldwin, et al.	372	43	1/25/96
	JM	5811319	9/22/98	Koike, et al.	438	46	3/26/96
	JN	5811931	9/22/98	Mueller-Mach, et al.	313	512	3/4/96
<i>BWB</i>	JO	5812105	9/22/98	Van De Ven,	345	83	6/10/96

Examiner:

Date Considered: 9/15/01

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Attorney Docket No.: NICHIA-00700

Serial No.:09/463643

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(37 CFR § 1.98(b))

Applicant: Shuji Nakamura, et al.

Filing Date: January 25, 2000

Group Art Unit: 2815

<i>BWB</i>	JP	5812570	9/22/98	Spaeth	372	36	9/30/96
	JQ	5814870	9/29/98	Spaeth	257	433	1/6/97
	JR	5818861	10/6/98	Tan, et al.	372	46	7/19/96
	JS	5828684	10/27/98	Van De Walle	372	45	12/29/95
	JT	5831288	11/3/98	Singh, et al.	257	77	9/29/97
	JU	5835514	11/10/98	Yuen, et al.	372	36	1/25/96
	JV	5835522	11/10/98	King, et al.	372	97	11/19/96
	JW	5837561	11/17/98	Kish, Jr., et al.	438	47	5/23/97
	JX	5838706	11/17/98	Edmond, et al.	372	45	11/19/96
	JY	5838707	11/17/98	Ramdani, et al.	372	45	12/27/96
	JZ	5838708	11/17/98	Lin, et al.	372	50	8/1/95
	KA	5846844	12/8/98	Akasaki, et al.	437	21	2/7/96
	KB	5847507	12/8/98	Butterworth, et al.	313	512	7/14/97
	KC	5850410	12/15/98	Kuramata	372	43	3/18/96
	KD	5855924	1/5/99	Lumbard	425	116	12/27/95
	KE	5858277	1/12/99	Chau, et al.	252	301.4 F	12/23/92
	KF	5859496	1/12/99	Murazaki, et al.	313	485	5/10/96
	KG	5861190	1/19/99	Greene, et al.	427	248.1	3/25/96
	KH	5861713	1/19/99	Kondo, et al.	313	495	6/26/97
	KI	5862167	1/19/99	Sassa, et al.	372	45	5/27/97
	KJ	5867516	2/2/99	Corzine, et al.	372	45	3/12/96
	KK	5868837	2/9/99	Disalvo, et al.	117	952	1/13/98
	KL	5877558	3/2/99	Nakamura, et al.	257	749	12/19/97
	KM	5879587	3/9/99	Yale	252	301.45	9/24/97
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	KO	5880486	3/9/99	Nakamura, et al.	257	96	8/30/96
	KP	5889802	3/30/99	Walker	372	31	3/27/97
	RQ	5889806	3/30/99	Nagai, et al.	372	45	8/8/97
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	KS	5892787	4/6/99	Tan, et al.	372	96	4/22/96
	RT	5900650	5/4/99	Nitta	257	94	7/2/97
	KU	5905276	5/18/99	Manabe, et al.	257	103	11/6/97
	KV	5907151	5/25/99	Gramann, et al.	250	214.1	5/27/97
	KW	5912477	6/15/99	Negley	257	95	5/20/97
	KX	5917202	6/29/99	Haitz, et al.	257	98	12/21/95
<i>BWB</i>	KY	5919422	7/6/99	Yamanaka, et al.	422	121	7/26/96

Examiner:

*Shuji Nakamura*

Date Considered: 9/15/01

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Applicant: Shuji Nakamura, et al.

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2815

BWB	KZ	5920766	7/6/99	Floyd	438	35	1/7/98
	LA	5923053	7/13/99	Jakowetz, et al.	257	95	9/30/96
	LB	5923118	6/13/99	Jennato, et al.	313	485	3/7/97
	LC	5923690	7/13/99	Kume, et al.	372	46	1/24/97
	LD	5923946	7/13/99	Negley	438	4	4/17/97
	LE	5925898	7/20/99	Spath	257	98	1/26/98
	LF	5927995	7/27/99	Chen, et al.	438	517	4/9/97
	LG	5935705	8/10/99	Chen, et al.	428	367	10/15/97
	LH	5936985	8/10/99	Yamamoto, et al.	372	38	9/13/95
	LI	5945689	8/31/99	Koike, et al.	257	88	3/18/96
	LJ	5953361	9/14/99	Borchert, et al.	372	96	11/25/97
	LK	5953581	9/14/99	Yamasaki, et al.	438	22	4/17/97
	LL	5958295	9/28/99	Yale	252	301.4 S	9/24/97
	LM	5959316	9/28/99	Lowery	257	98	9/1/98
	LN	5959401	9/28/99	Asami, et al.	313	503	5/21/97
	LO	5961723	10/5/99	Roithner, et al.	118	715	11/26/96
	LP	5964943	10/12/99	Stein, et al.	117	88	6/25/97
	LQ	5966393	10/12/99	Hide, et al.	372	23	2/4/97
	LR	5968265	10/19/99	Stein, et al.	117	71	1/27/98
	LS	5969378	10/19/99	Singh	257	77	7/10/97
	LT	5972781	10/26/99	Wegleiter, et al.	438	460	9/30/97
	LU	5972801	10/26/99	Lipkin, et al.	438	770	11/8/95
	LV	5973336	10/26/99	Hanke, et al.	257	94	11/3/97
	LW	5980631	11/9/99	Tews, et al.	117	89	12/17/97
	LX	5981945	11/9/99	Spaeth, et al.	250	239	3/8/96
	LY	5981979	11/9/99	Brunner	257	99	11/26/97
	LZ	5982970	11/9/99	Schneider	385	125	9/19/97
	MA	5986317	11/16/99	Wiese	257	433	9/29/95
	MB	5991160	11/23/99	Lumbard	361	760	12/27/95
	MC	5994722	11/30/99	Averbeck, et al.	257	89	6/30/98
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	MF	Document Number	Publication Date	Country / Patent Office	Class	Subclass	Translation
	MG	CA1325582	12/28/93	CA	HO1L	21/36B	
NR	MH	EP0356059A2	2/28/90	EP	HO1L	21/38	

Examiner: *B. han Baum*Date Considered: *2/15/01*

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Attorney Docket No.: NICHIA-00700 Serial No.:09/463643

Applicant: Shuji Nakamura, et al.

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<i>BWB</i>	MI	EP0356059A3	2/28/90	EP	HO1L	21/38	
	MJ	EP0380340A2	8/1/90	EP	HO1L	29/91	
	MK	EP0380340A3	8/1/90	EP	HO1L	29/91	
	ML	EP0637069A1	2/1/95	EP	HO1L	21/473	
	MM	EP0731512A2	9/11/96	EP	HO1L	33/00	
	MN	EP0731512A3	7/2/97	EP	HO1L	33/00	
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	MT	EP0905799A2	3/31/99	EP	HO1L	33/00	
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	MV	FR2613136	9/30/88	FR	HO1L	33/00	
	MW	GB2322737A	3/2/98	GB	HO1L	21/304	
	MX	GB2323210A	9/16/98	GB	HO1L	33/00	
	MY	JP05152609	6/18/93	JP	HO1L	33/00	
<i>BWB</i>	MZ	JP0766192	3/10/95	JP	<i>SAVO TRANSLATIONS</i>		HO1L 29/78
	NA	JP09193137	7/29/97	JP	B28D	5/044	
	NB	JP10233529	2/14/97	JP	HO1L	33/00	
<i>BWB</i>	NC	JP1064854	7/18/96	JP	HO1L	21/301	
	ND	JP7176794	7/14/95	JP	HO1L	33/00	
	NE	WO9702478A1	1/23/97	PCT	G01M	19/00	
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	NL	WO9812757A1	3/26/98	PCT	HO1L	33/00	
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Examiner: *Ryan Baum*Date Considered: *9/15/01*

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Attorney Docket No.: NICHIA-00700 Serial No.:09/463643

Applicant: Shuji Nakamura, et al.

## INFORMATION Disclosure Statement by Applicant

(37 CFR § 1.98(b))

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<i>BWB</i>	NS	WO9857378A1	12/17/98	PCT	HOIL	29/73	
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Examiner: <i>Brian Bent</i>	Date Considered: <i>9/15/01</i>
EXAMINER: <i>Brian Bent</i>	Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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SERIAL NO.

925-178

09/463,643

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R ShultzINFORMATION DISCLOSURE  
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AKAMURA et al

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Examiner

*John B. Bartz*

Date Considered

5/30/02

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BMB	5,903,017	5/1999	Itaya et al			

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			CLASS	SUBCLASS	YES NO
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Examiner

*Brian Palmer*

Date Considered

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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

428 Rec'd PCT/PTR 25 JAN 2000

Sheet 1 of 1

FORM PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No.: NICJIIA-00700	Serial No. 09/463643
INFORMATION-DISCLOSURE STATEMENT BY APPLICANT (Use Several Sheets If Necessary)		Applicant: Shuji Nakamura et al.	
(37 CFR § 1.98(b))		Filing Date: January 25, 2000	Group Art Unit: 2815

## U.S. PATENT DOCUMENTS

Examiner Initials	Serial / Patent Number	Issue Date	Applicant / Patentee	Class	Subclass	Filing Date
AA						
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## FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

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						Yes	No
BWB	AK	9-116130	5/2/97	Japan	H01L	29/43	X
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EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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FORM PTO-1449 (Modified) <i>Patent &amp; Trademark Office</i> <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use Several Sheets If Necessary) (37 CFR § 1.98(b))				U.S. Department of Commerce Patent and Trademark Office Attorney Docket No.: NICHIA-00700 Serial No.: 09/463,643	
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							Yes	No
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EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.